BC33725TAR 全部高亮显示 区分大小写 字词匹配 第1项,共匹配1项



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BC337 / BC338 NPN Epitaxial Silicon Transistor

Features

- · Switching and Amplifier Applications
- · Suitable for AF-Driver Stages and Low-Power Output Stages
- · Complement to BC327 / BC328



Ordering Information

Part Number	Top Mark	Package	Packing Method
BC33716BU	BC33716	TO-92 3L	Bulk
BC33716TA	BC33716	TO-92 3L	Ammo
BC33716TFR	BC33716	TO-92 3L	Tape and Reel
BC33725BU	BC33725	TO-92 3L	Bulk
BC33725TA	BC33725	TO-92 3L	Ammo
BC33725TAR	BC33725	TO-92 3L	Ammo
BC33725TF	BC33725	TO-92 3L	Tape and Reel
BC33725TFR	BC33725	TO-92 3L	Tape and Reel
BC33740BU	BC33740	TO-92 3L	Bulk
BC33740TA	BC33740	TO-92 3L	Ammo
BC33825TA	BC33825	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
	Collector Essitter Voltage	BC337	50	V
V_{CES}	Collector-Emitter Voltage	BC338	30	
\/	Collector Emitter Voltage	BC337	45	V
V _{CEO}	Collector-Emitter Voltage	BC338	25	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current (DC)		800	mA
T _J	Junction Temperature		150	°C
T _{STG}	Storage Temperature	-55 to 150	°C	

Thermal Characteristics(1)

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
D_	Power Dissipation	625	mW
P _D	Derate Above 25°C	5.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	°C/W

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
D\/	Collector-Emitter	BC337	L = 10 m 1 L = 0	45			V
BV _{CEO}	Breakdown Voltage	BC338	$I_C = 10 \text{ mA}, I_B = 0$	25			v
D\/	Collector-Emitter	BC337	I _C = 0.1 mA, V _{BE} = 0	50			V
BV _{CES}	Breakdown Voltage	BC338		30			
BV _{EBO}	Emitter-Base Breakdown Vol	tage	I _E = 0.1 mA, I _C = 0	5			V
1	Collector Cut-Off Current	BC337	V _{CE} = 45 V, I _B = 0		2	100	nA
I _{CES}		BC338	V _{CE} = 25 V, I _B = 0		2	100	IIA
h _{FE1}	DC Current Gain		V _{CE} = 1 V, I _C = 100 mA	100		630	
h _{FE2}			V _{CE} = 1 V, I _C = 300 mA	60			
V _{CE} (sat)	Collector-Emitter Saturation Voltage		I _C = 500 mA, I _B = 50 mA			0.7	V
V _{BE} (on)	Base-Emitter On Voltage		V _{CE} = 1 V, I _C = 300 mA			1.2	V
f _T	Current Gain Bandwidth Product		V _{CE} = 5 V, I _C = 10 mA, f = 50 MHz		100		MHz
C _{ob}	Output Capacitance		V _{CB} = 10 V, I _E = 0, f = 1 MHz		12		pF

h_{FE} Classification

Classification	16	25	40	
h _{FE1}	100 ~ 250	160 ~ 400	250 ~ 630	
h _{FE2}	60 ~	100 ~	170 ~	